









	<h2 style="color: red;">FQB3N30TM</h2>	
	Hersteller-Teilenummer:	FQB3N30TM
	Hersteller / Marke:	AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung:	MOSFET N-CH 300V 3.2A D2PAK
Datenblätter:	 FQB3N30TM.pdf	
RoHS Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 34226 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	FQB3N30TM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 300V 3.2A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	34226 pcs Stock
detaillierte Beschreibung	N-Channel 300V 3.2A (Tc) 3.13W (Ta), 55W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 55W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	300V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.2A (Tc)
Rds On (Max) @ Id, Vgs	2.2 Ohm @ 1.6A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	7nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	230pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)














































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Sie können auch interessiert sein:

 <p>FQB3N25TM Fairchild/ON Semiconductor MOSFET N-CH 250V 2.8A D2PAK</p>	 <p>FQB3N30TM Fairchild/ON Semiconductor MOSFET N-CH 300V 3.2A D2PAK</p>	 <p>FQB3N30 VB FQB3N30 VB</p>	 <p>FQB3N25TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 250V 2.8A D2PAK</p>
 <p>FQB3N25 VB FQB3N25 VB</p>	 <p>FQB3N40TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 400V 2.5A D2PAK</p>	 <p>FQB3N40TM Fairchild/ON Semiconductor MOSFET N-CH 400V 2.5A D2PAK</p>	 <p>FQB3N60C FCS FQB3N60C FCS</p>

heiße Teile

Mehr

 FQB32N12V2TM	 FQB32N12V2TM	 FQB32N20	 FQB32N20C	 FQB32N20CTM
 FQB32N20CTM	 FQB32N30	 FQB33N10	 FQB33N10L	 FQB33N10LTM
 FQB33N10LTM	 FQB33N10TM	 FQB33N10TM	 FQB34N20	 FQB34N20L
 FQB34N20LTM	 FQB34N20LTM	 FQB34N20TM	 FQB34N20TM_AM002	 FQB34P10
 FQB34P10TM	 FQB34P10TM	 FQB34P10TM_F085	 FQB3N25TM	 FQB3N25TM
 FQB3N30TM	 FQB3N40TM	 FQB3N40TM	 FQB3N60C	 FQB3N80TM
 FQB3N80TM	 FQB3N90TM	 FQB3N90TM	 FQB3P20TM	 FQB3P20TM
 FQB3P50TM	 FQB3P50TM	 FQB44N10	 FQB44N10TM	 FQB44N10TM
 FQB46N15	 FQB46N15TM	 FQB47P06	 FQB47P06TM	 FQB4N20L
 FQB4N20LTM	 FQB4N20LTM	 FQB4N20TM	 FQB4N20TM	 FQB4N25TM

Contact us: Info@Y-IC.com

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